

isc Silicon PNP Darlington Power Transistor

ST26025A

DESCRIPTION

- Collector-Emitter Breakdown Voltage-
: $V_{(BR)CEO} = -100V(\text{Min.})$
- High DC Current Gain-
: $h_{FE} = 750(\text{Min.})@I_C = -10A$
- Low Collector Saturation Voltage-
: $V_{CE(sat)} = -3.0V(\text{Max.})@I_C = -20A$

APPLICATIONS

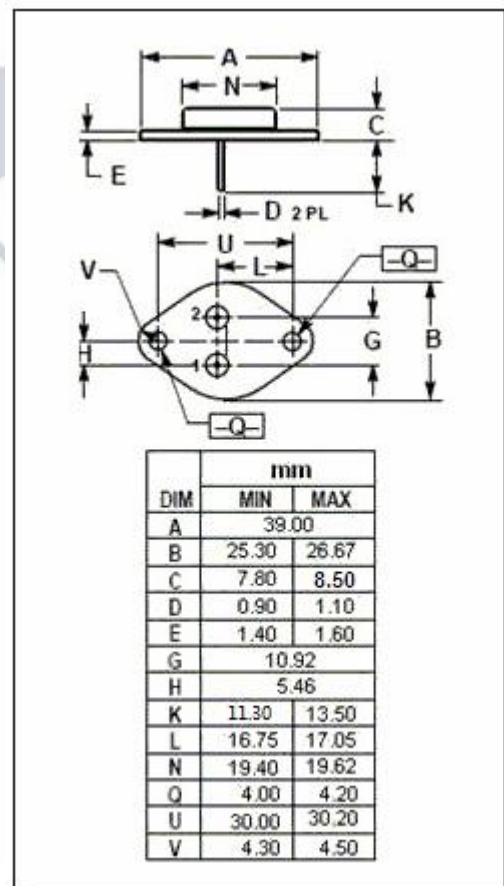
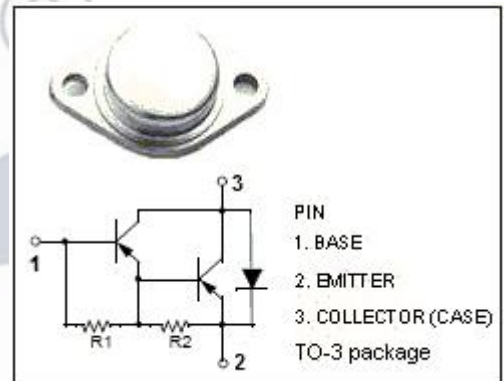
- Designed for use as output devices in complementary general purpose amplifier applications.

ABSOLUTE MAXIMUM RATINGS ($T_a=25^\circ C$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	-120	V
V_{CEO}	Collector-Emitter Voltage	-100	V
V_{EBO}	Emitter-Base Voltage	-5	V
I_C	Collector Current-Continuous	-20	A
I_B	Base Current-Continuous	-1	A
P_C	Collector Power Dissipation @ $T_c=25^\circ C$	160	W
T_j	Junction Temperature	200	$^\circ C$
T_{stg}	Storage Temperature Range	-55~+200	$^\circ C$

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
$R_{th\ j-c}$	Thermal Resistance, Junction to Case	0.87	$^\circ C/W$



isc Silicon PNP Darlington Power Transistor**ST26025A****ELECTRICAL CHARACTERISTICS** $T_C=25^\circ\text{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage	$I_C = -50\text{mA}; I_B = 0$	-100			V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C = -20\text{A}; I_B = -0.2\text{A}$			-3.0	V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage	$I_C = -20\text{A}; I_B = -0.2\text{A}$			-3.5	V
I_{CBO}	Collector Cutoff Current	$V_{CB} = -120\text{V}; I_E = 0$ $V_{CB} = -120\text{V}; I_E = 0; T_C = 150^\circ\text{C}$			-1.0 -5.0	mA
I_{CEO}	Collector Cutoff Current	$V_{CE} = -100\text{V}; I_B = 0$			-1.0	mA
I_{EBO}	Emitter Cutoff Current	$V_{EB} = -5\text{V}; I_C = 0$			-5.0	mA
h_{FE}	DC Current Gain	$I_C = -10\text{A}, V_{CE} = -3\text{V}$	750			